

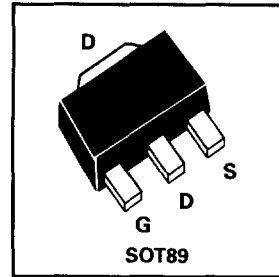
# SOT89 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 3 - NOVEMBER 1995



## FCX596

PARTMARKING DETAIL - P96



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-220	V
Collector-Emitter Voltage	$V_{CEO}$	-200	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-1	A
Continuous Collector Current	$I_C$	-0.3	A
Base Current	$I_B$	-200	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	$P_{tot}$	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-65 to +150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ ).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-220		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$		-100	nA	$V_{CB} = -200\text{V}$
Emitter Cut-Off Current	$I_{EBO}$		-100	nA	$V_{EB} = -4\text{V}$
Collector-Emitter Cut-Off Current	$I_{CES}$		-100	nA	$V_{CES} = -200\text{V}$
Saturation Voltages	$V_{CE(sat)}$		-0.2 -0.35	V	$I_C = -100\text{mA}, I_B = -10\text{mA}$ $I_C = -250\text{mA}, I_B = -25\text{mA}^*$
	$V_{BE(sat)}$		-1.0	V	$I_C = -250\text{mA}, I_B = -25\text{mA}^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-0.9	V	$I_C = -250\text{mA}, V_{CE} = -10\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100 100 85 35	300		$I_C = -1\text{mA}, V_{CE} = -10\text{V}$ $I_C = -100\text{mA}, V_{CE} = -10\text{V}^*$ $I_C = -250\text{mA}, V_{CE} = -10\text{V}^*$ $I_C = -400\text{mA}, V_{CE} = -10\text{V},$
Transition Frequency	$f_T$	150		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	$C_{obo}$		10	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

For typical Characteristics graphs see FMMT596 datasheet.